

2SK663

Silicon N-Channel Junction FET

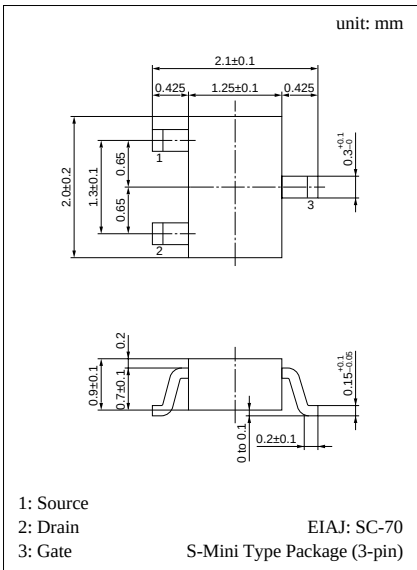
For low-frequency amplification
For switching

■ Features

- Low noise-figure (NF)
- High gate to drain voltage V_{GDO}
- S-mini type package, allowing downsizing of the sets and automatic insertion through the tape/magazine packing.

■ Absolute Maximum Ratings ($T_a = 25^\circ\text{C}$)

Parameter	Symbol	Ratings	Unit
Drain to Source voltage	V_{DSX}	55	V
Gate to Drain voltage	V_{GDO}	-55	V
Gate to Source voltage	V_{GSO}	-55	V
Drain current	I_D	30	mA
Gate current	I_G	10	mA
Allowable power dissipation	P_D	150	mW
Junction temperature	T_j	125	$^\circ\text{C}$
Storage temperature	T_{stg}	-55 to +125	$^\circ\text{C}$



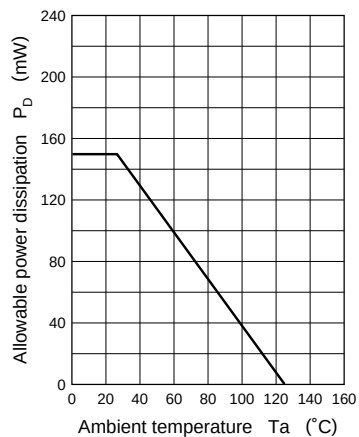
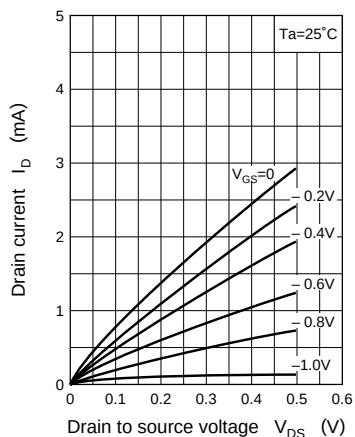
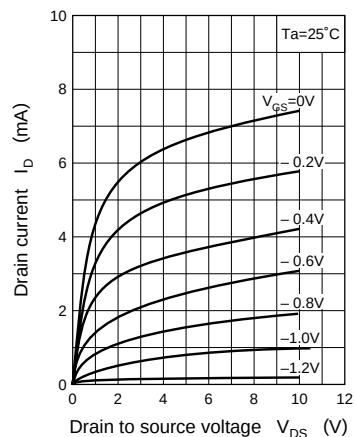
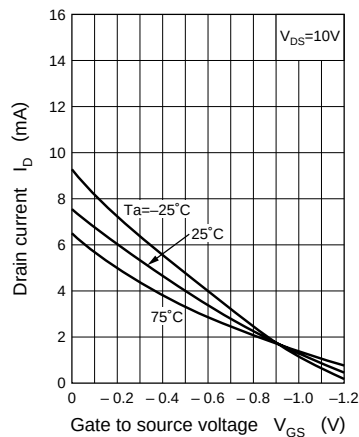
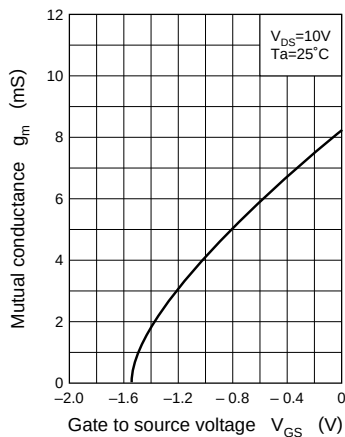
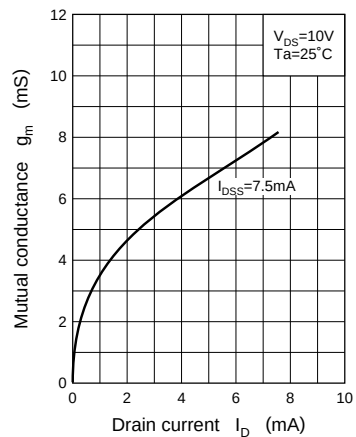
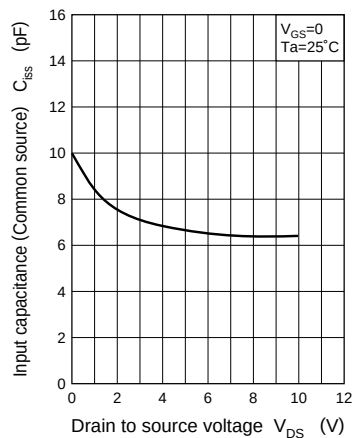
Marking Symbol (Example): 2B

■ Electrical Characteristics ($T_a = 25^\circ\text{C}$)

Parameter	Symbol	Conditions	min	typ	max	Unit
Drain to Source cut-off current	I_{DSS}^*	$V_{DS} = 10\text{V}, V_{GS} = 0$	1		12	mA
Gate to Source leakage current	I_{GSS}	$V_{GS} = -30\text{V}, V_{DS} = 0$			-10	nA
Gate to Drain voltage	V_{GDS}	$I_G = 100\mu\text{A}, V_{DS} = 0$	55	80		V
Gate to Source cut-off voltage	V_{GSC}	$V_{DS} = 10\text{V}, I_D = 10\mu\text{A}$			-5	V
Mutual conductance	g_m	$V_{DS} = 10\text{V}, I_D = 5\text{mA}, f = 1\text{kHz}$	2.5	7.5		mS
Input capacitance (Common Source)	C_{iss}	$V_{DS} = 10\text{V}, V_{GS} = 0, f = 1\text{MHz}$		6.5		pF
Reverse transfer capacitance (Common Source)	C_{rss}			1.9		pF
Noise figure	NF	$V_{DS} = 10\text{V}, V_{GS} = 0, R_g = 100\text{k}\Omega, f = 100\text{Hz}$		2.5		dB

* I_{DSS} rank classification

Runk	P	Q	R
I_{DSS} (mA)	1 to 3	2 to 6.5	5 to 12
Marking Symbol	2BP	2BQ	2BR

$P_D - T_a$  $I_D - V_{DS}$  $I_D - V_{DS}$  $I_D - V_{GS}$  $g_m - V_{GS}$  $g_m - I_D$  $C_{iss} - V_{DS}$  $C_{oss} - V_{DS}$ 